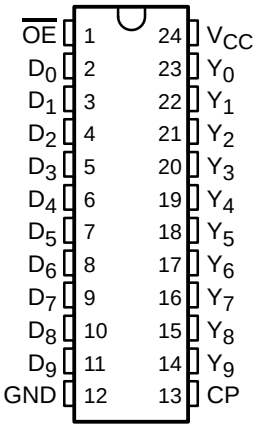
- **Function, Pinout, and Drive Compatible With FCT, F Logic, and AM29821**
- **Reduced V_{OH} (Typically = 3.3 V) Version of Equivalent FCT Functions**
- **Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Matched Rise and Fall Times**
- **Fully Compatible With TTL Input and Output Logic Levels**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**
- **64-mA Output Sink Current**
  32-mA Output Source Current
- **High-Speed Parallel Register With Positive-Edge-Triggered D-Type Flip-Flops**
- **3-State Outputs**

P, Q, OR SO PACKAGE
(TOP VIEW)



description

This bus-interface register is designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The CY74FCT821T is a 10-bit-wide buffered version of the popular CY74FCT374 function. This device is ideal for use as an output port requiring high I_{OL}/I_{OH}.

This device is designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. Outputs are designed for low-capacitance bus loading in the high-impedance state.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

PIN DESCRIPTION

NAME	I/O	DESCRIPTION
D	I	D flip-flop data inputs
CP	O	Clock pulse for the register. Enters data into the register on the low-to-high clock transition.
Y	O	Register 3-state outputs
$\overline{OE}$	I	Output control. When $\overline{OE}$ is high, the Y outputs are in the high-impedance state. When $\overline{OE}$ is low, true register data is present at the Y outputs.

ORDERING INFORMATION

T_A	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QSOP – Q	Tape and reel	6	CY74FCT821CTQCT	FCT821C
	SOIC – SO	Tube	6	CY74FCT821CTSOC	FCT821C
		Tape and reel	6	CY74FCT821CTSOCT	
	DIP – P	Tube	7.5	CY74FCT821BTPC	CY74FCT821BTPC
	SOIC – SO	Tube	7.5	CY74FCT821BTSOC	FCT821B
		Tape and reel	7.5	CY74FCT821BTSOCT	
	QSOP – Q	Tape and reel	10	CY74FCT821ATQCT	FCT821A
	SOIC – SO	Tube	10	CY74FCT821ATSOC	FCT821A
		Tape and reel	10	CY74FCT821ATSOCT	

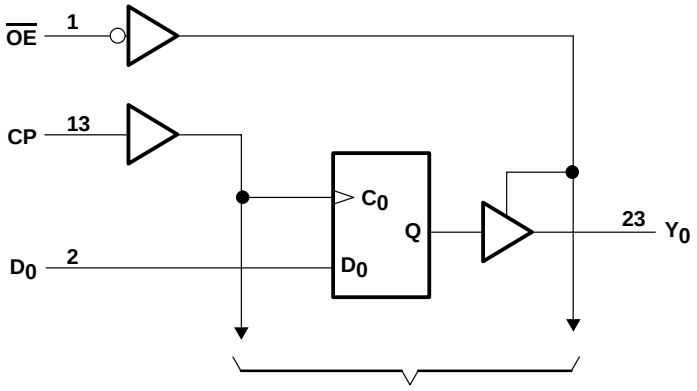
† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

INPUTS			INTERNAL OUTPUTS		FUNCTION
$\overline{OE}$	D	CP	Q	Y	
H	X	↑	L	Z	Z
H	L	↑	L	Z	Load
H	H	↑	H	Z	
L	L	↑	L	L	
L	H	↑	H	H	

H = High logic level, L = Low logic level, X = Don't care,
↑ = Low-to-high transition, Z = High-impedance state

logic diagram (positive logic)



absolute maximum rating over operating free-air temperature range (unless otherwise noted)†

Supply voltage range to ground potential . . . . . –0.5 V to 7 V
DC input voltage range . . . . . –0.5 V to 7 V
DC output voltage range . . . . . –0.5 V to 7 V
DC output current (maximum sink current/pin) . . . . . 120 mA
Package thermal impedance, θ_{JA} (see Note 1): P package . . . . . 67°C/W
(see Note 2): Q package . . . . . 61°C/W
(see Note 2): SO package . . . . . 46°C/W
Ambient temperature range with power applied, T_A . . . . . –65°C to 135°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The package thermal impedance is calculated in accordance with JESD 51-3.
2. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 3)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	4.75	5	5.25	V
V_{IH}	High-level input voltage	2			V
V_{IL}	Low-level input voltage			0.8	V
I_{OH}	High-level output current			–32	mA
I_{OL}	Low-level output current			64	mA
T_A	Operating free-air temperature	–40		85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}	V_{CC} = 4.75 V,	I_{IN} = –18 mA			–0.7	–1.2	V
V_{OH}	V_{CC} = 4.75 V	I_{OH} = –32 mA		2			V
		I_{OH} = –15 mA		2.4	3.3		
V_{OL}	V_{CC} = 4.75 V,	I_{OL} = 64 mA			0.3	0.55	V
V_{hys}	All inputs				0.2		V
I_I	V_{CC} = 5.25 V,	V_{IN} = V_{CC}				5	µA
I_{IH}	V_{CC} = 5.25 V,	V_{IN} = 2.7 V				±1	µA
I_{IL}	V_{CC} = 5.25 V,	V_{IN} = 0.5 V				±1	µA
I_{OZH}	V_{CC} = 5.25 V,	V_{OUT} = 2.7 V				10	µA
I_{OZL}	V_{CC} = 5.25 V,	V_{OUT} = 0.5 V				–10	µA
I_{OS}‡	V_{CC} = 5.25 V,	V_{OUT} = 0 V		–60	–120	–225	mA
I_{off}	V_{CC} = 0 V,	V_{OUT} = 4.5 V				±1	µA
I_{CC}	V_{CC} = 5.25 V,	V_{IN} ≤ 0.2 V,	V_{IN} ≥ V_{CC} – 0.2 V		0.1	0.2	mA
ΔI_{CC}	V_{CC} = 5.25 V, V_{IN} = 3.4 V§, f_1 = 0, Outputs open				0.5	2	mA
I_{CCD}¶	V_{CC} = 5.25 V, One bit switching at 50% duty cycle, Outputs open, $\overline{OE}$ = $\overline{EN}$ = GND, V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V				0.06	0.12	mA/ MHz
I_C#	V_{CC} = 5.25 V, Outputs open, $\overline{OE}$ = $\overline{EN}$ = GND	One bit switching at f_1 = 5 MHz at 50% duty cycle	V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V		0.7	1.4	mA
			V_{IN} = 3.4 V or GND		1.2	3.4	
		Eight bits switching at f_1 = 2.5 MHz at 50% duty cycle	V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V		1.6	3.2‖	
			V_{IN} = 3.4 V or GND		3.9	12.2‖	
C_i					5	10	pF
C_o					9	12	pF

† Typical values are at V_{CC} = 5 V, T_A = 25°C.

‡ Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

§ Per TTL-driven input (V_{IN} = 3.4 V); all other inputs at V_{CC} or GND

¶ This parameter is derived for use in total power-supply calculations.

$I_C = I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD} (f_0/2 + f_1 \times N_1)$

Where:

I_C = Total supply current
I_{CC} = Power-supply current with CMOS input levels
ΔI_{CC} = Power-supply current for a TTL high input (V_{IN} = 3.4 V)
D_H = Duty cycle for TTL inputs high
N_T = Number of TTL inputs at D_H
I_{CCD} = Dynamic current caused by an input transition pair (HLH or LHL)
f_0 = Clock frequency for registered devices, otherwise zero
f_1 = Input signal frequency
N_1 = Number of inputs changing at f_1

All currents are in milliamperes and all frequencies are in megahertz.

‖ Values for these conditions are examples of the I_{CC} formula.

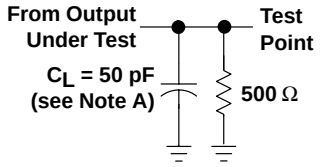
timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER			TEST LOAD	CY74FCT821AT		CY74FCT821BT		CY74FCT821CT		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	CP	C_L = 50 pF, R_L = 500 Ω	7		6		6		ns
t_{su}	Setup time, before CP↑	Data	C_L = 50 pF, R_L = 500 Ω	4		3		3		ns
t_h	Hold time, after CP↑	Data	C_L = 50 pF, R_L = 500 Ω	2		1.5		1.5		ns

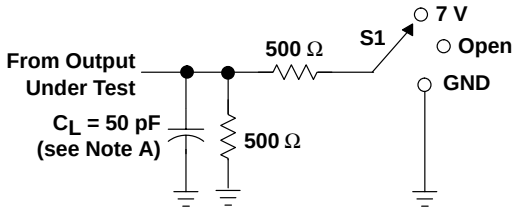
switching characteristics over operating free-air temperature range (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST LOAD	CY74FCT821AT		CY74FCT821BT		CY74FCT821CT		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	CP	Y	C_L = 50 pF, R_L = 500 Ω		10		7.5		6	ns
t_{PHL}					10		7.5		6	
t_{PLH}	CP	Y	C_L = 300 pF, R_L = 500 Ω		20		15		12.5	ns
t_{PHL}					20		15		12.5	
t_{PZH}	$\overline{OE}$	Y	C_L = 50 pF, R_L = 500 Ω		12		8		7	ns
t_{PZL}					12		8		7	
t_{PZH}	$\overline{OE}$	Y	C_L = 300 pF, R_L = 500 Ω		23		15		12.5	ns
t_{PZL}					23		15		12.5	
t_{PHZ}	$\overline{OE}$	Y	C_L = 5 pF, R_L = 500 Ω		7		6.5		6	ns
t_{PLZ}					7		6.5		6	
t_{PHZ}	$\overline{OE}$	Y	C_L = 50 pF, R_L = 500 Ω		8		7.5		6.5	ns
t_{PLZ}					8		7.5		6.5	

PARAMETER MEASUREMENT INFORMATION

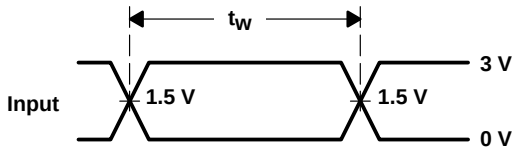


LOAD CIRCUIT FOR TOTEM-POLE OUTPUTS

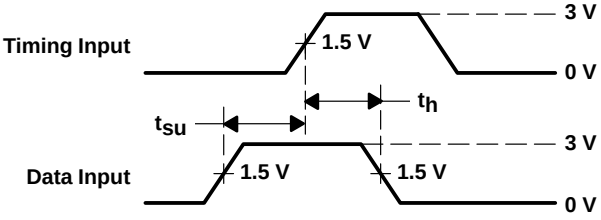


LOAD CIRCUIT FOR 3-STATE OUTPUTS

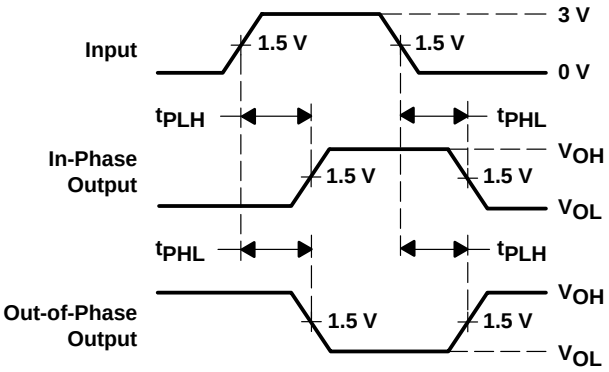
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open



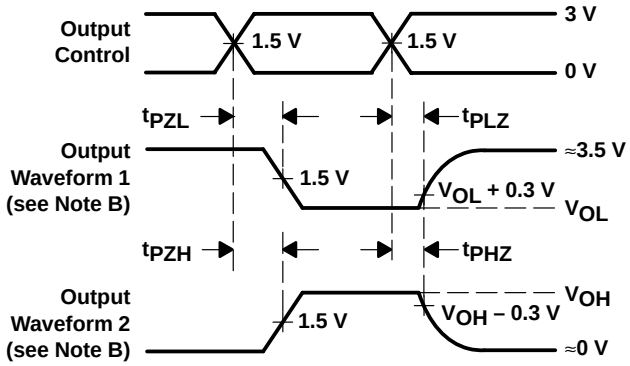
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CY74FCT821ATSOC	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821A	Samples
CY74FCT821BTSOC	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821B	Samples
CY74FCT821BTSOCE4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821B	Samples
CY74FCT821CTQCT	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT821C	Samples
CY74FCT821CTSOC	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C	Samples
CY74FCT821CTSOCT	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

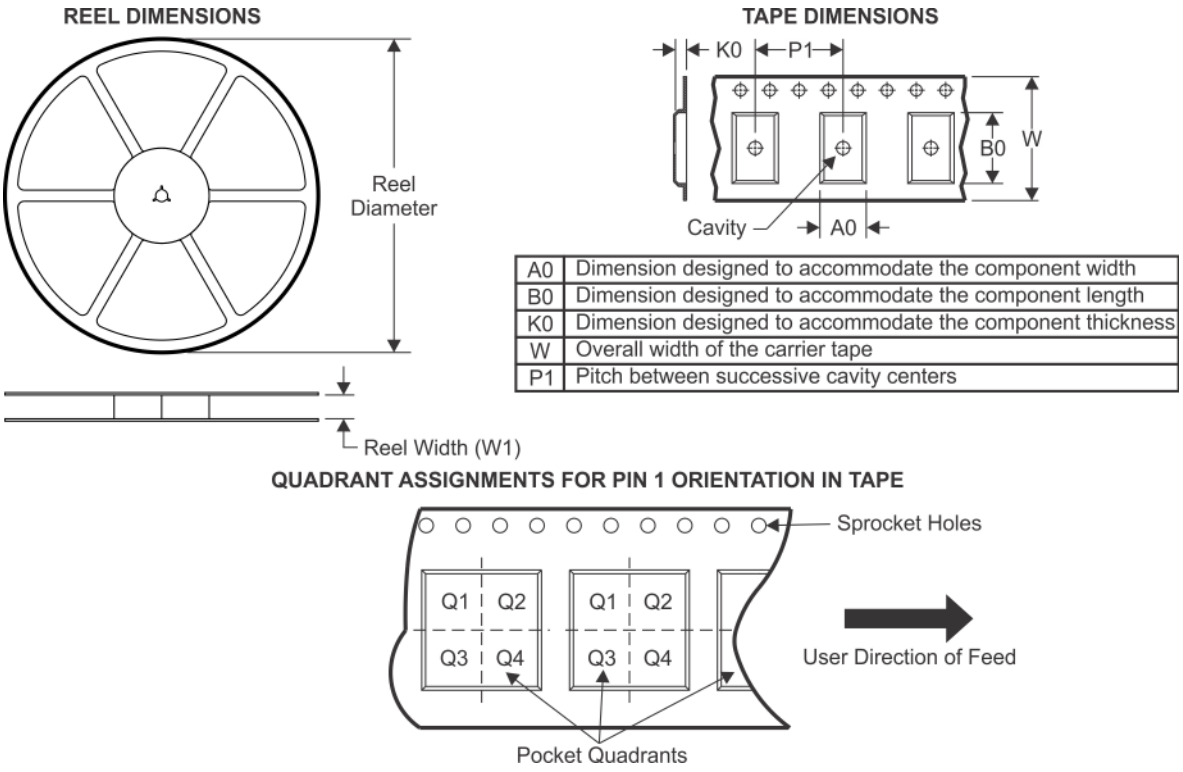
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

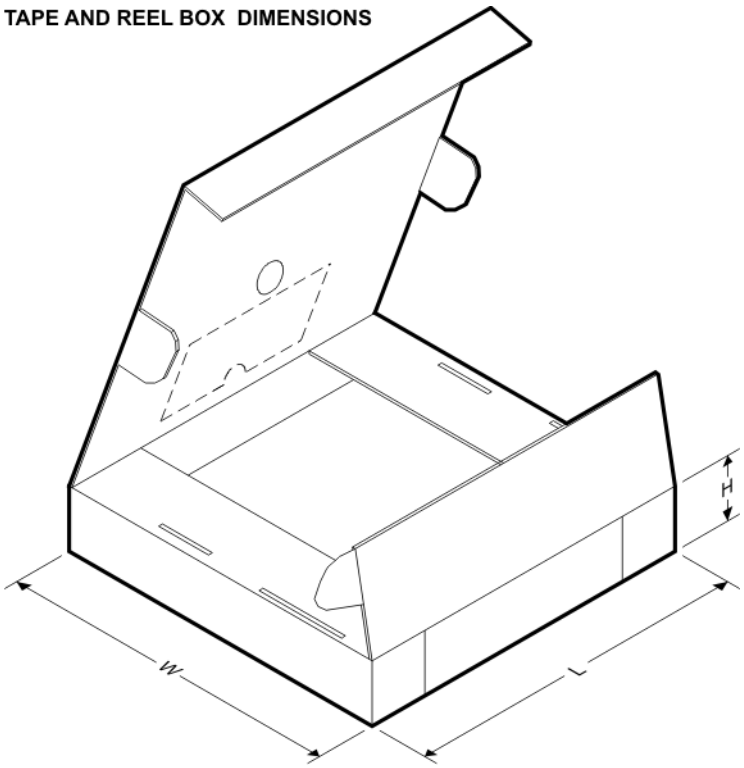


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT821CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT821CTSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

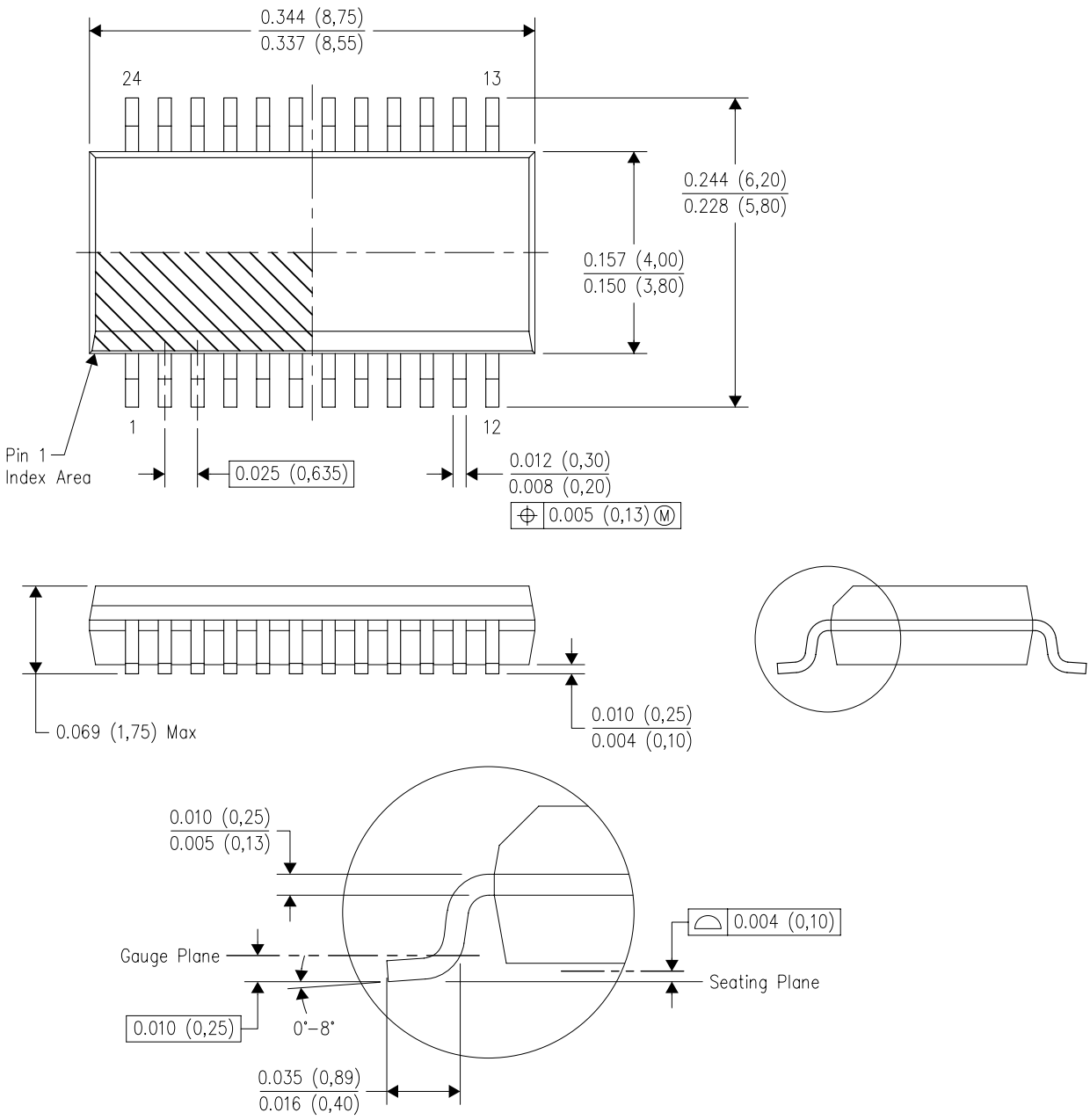
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

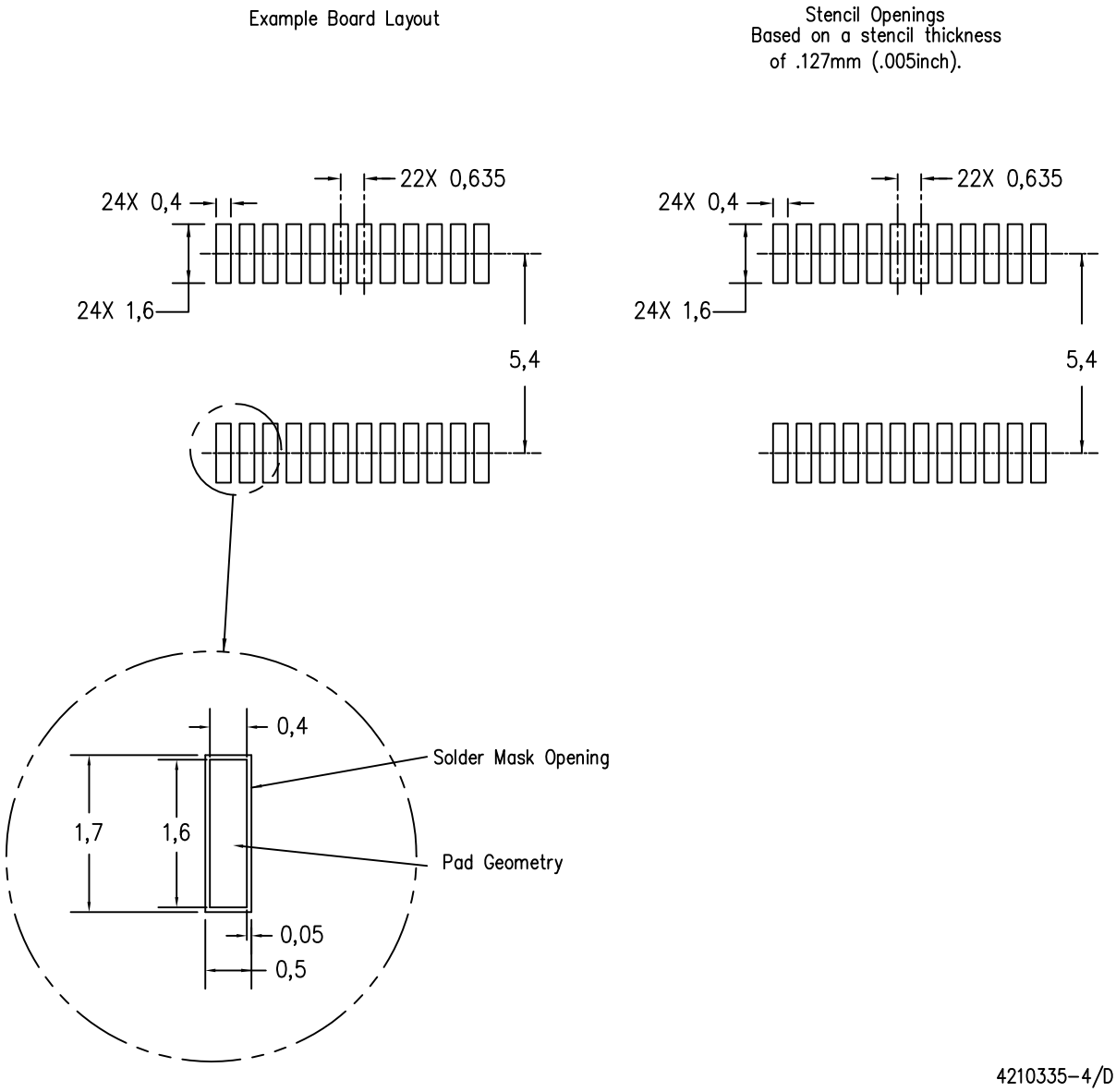
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT821CTQCT	SSOP	DBQ	24	2500	367.0	367.0	38.0
CY74FCT821CTSOCT	SOIC	DW	24	2000	350.0	350.0	43.0

DBQ (R–PDSO–G24) PLASTIC SMALL–OUTLINE PACKAGE



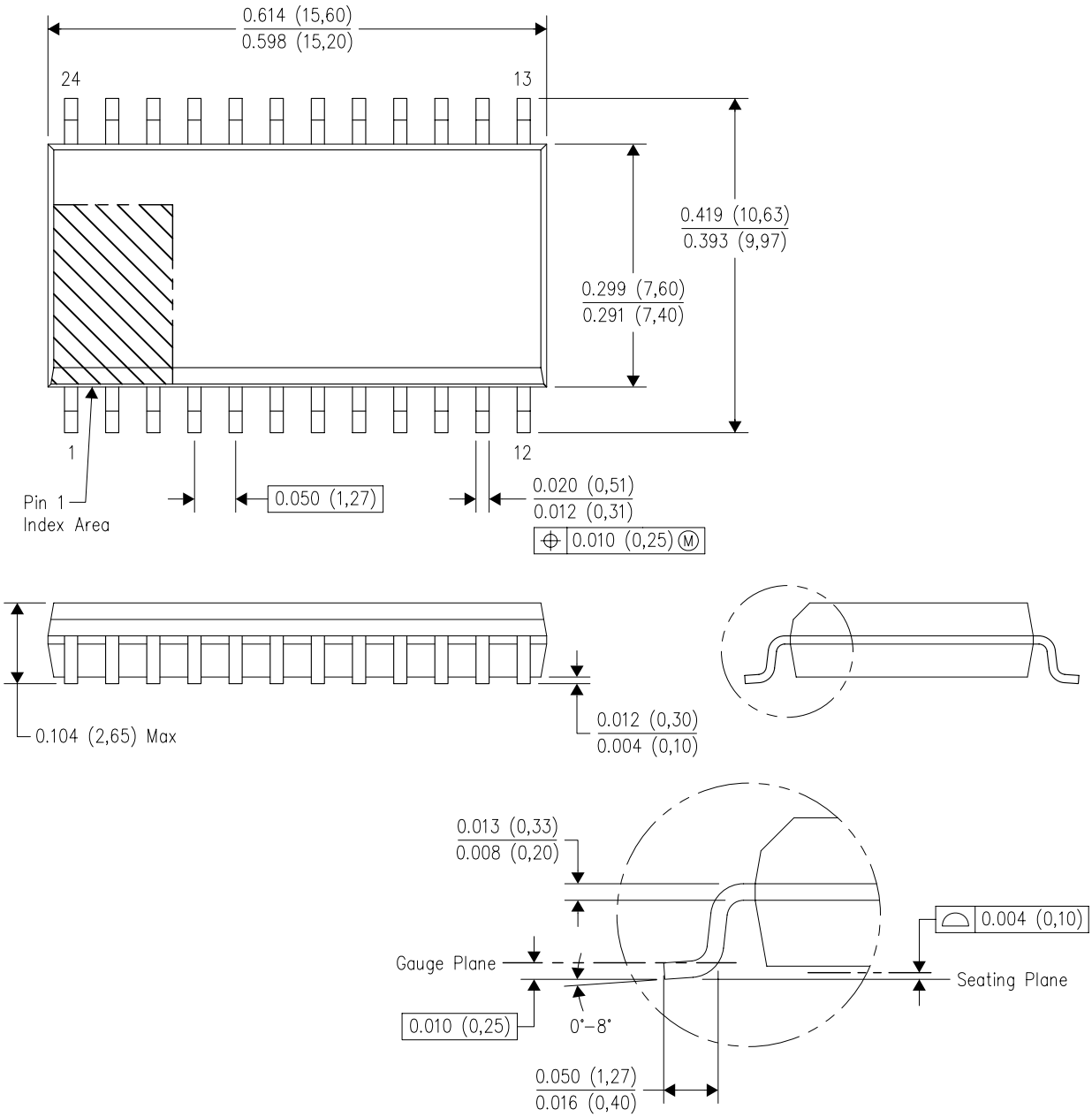
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
D. Falls within JEDEC MO–137 variation AE.

DBQ (R–PDSO–G24) PLASTIC SMALL OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AD.

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